

Dual Schmitt-Trigger Inverter

NLV27WZ14

The NLV27WZ14 is a high performance dual inverter with Schmitt-Trigger inputs operating from a 1.65 to 5.5 V supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.2 ns t_{PD} at $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88 and TSOP-6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS



SC-88 **DF SUFFIX** CASE 419B-02



MARKING DIAGRAMS



TSOP-6 CASE 318G-02



X, XXX = Specific Device Code

= Date Code*

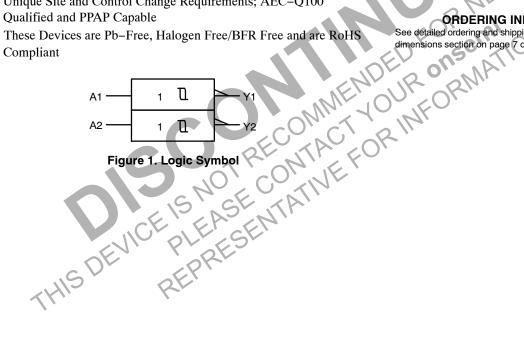
= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.



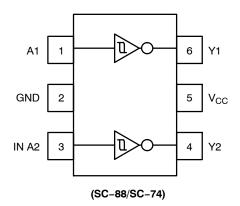


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

1 2 3 4 5 6	A1 GND A2 Y2 Vcc Y1	RECONTACE OF A THE PARTY OF A THE PA	ENDE TOR	D FOR ORI	WEN ON
3 4 5 6		2ECONNA 2ECONTAC	ENDE TOR		VEN OF
3 4 5 6	Y2 V _{CC} Y1	2ECONING	ENDE TOR	D FOR ORS	MEN
4 5 6	Y2 V _{CC} Y1	2ECONNA 2ECONTAC	ENDE TOR	D FOR ORS	MATION
5 6	V _{CC} Y1	2ECONINA 2ECONTAC	ENDE	D FOR	MATION
6	Y1	2ECOMPACE ON TAKE	ENDE TOR	DFORS JRORN	NATION
5	5 0	2ECONINA 2ECONTAC	ENDE TOR	JR ons	MATI
THIS DEVICE R	SNOE	COLINI			

FUNCTION TABLE

A Input	Y Output	
L	H	(\setminus)
I	L	

MAXIMUM RATINGS

Symbol	Characteristics		Value	Units
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Active-Mode (High or Low TSOP-6, SC-88 Tri-State Mode (Note Town Mode (VCC)	Vote 1)	-0.5 to V _{CC} +0.5 -0.5 to +7.0 -0.5 to +7.0	V
I _{IK}	DC Input Diode Current, V _{IN} < GND		-50	mA
lok	DC Output Diode Current, V _{OUT} < GND		-50	mA
l _{out}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88	377	°C/W
P_{D}	Power Dissipation in Still Air	SC-88	332	mW
MSL	Moisture Sensitivity		Level 1	1
F _R	Flamebility Rating Oxygen Index: 26	8 to 34	UL 94-V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3) Human Body Charged Device	Model Model	2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)	150	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality

- Stresses exceeding those listed in the Maximum Hatings rable may damage the device. If any or mese limits are exceeded, device lands and reliability may be affected.

 1. Applicable to devices with outputs that may be tri–stated.

 2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.

 3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Transition Rise or Fall Rate $ \begin{array}{c} V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \\ \end{array} $	0 0 0 0	No Limit No Limit No Limit No Limit	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

				T _A :	= 25°C		-40°C ≤ T _A	≤ 85°C	-55°C ≤ T _A ≤	≤ 125°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _T +	Positive Input		1.65	0.6	1.0	1.4	0.6	1.4	0.6	1.4	V
	Threshold Voltage		2.3	1.0	1.5	1.8	1.0	1.8	1.0	1.8	
			2.7	1.2	1.7	2.0	1.2	2.0	1.2	2.0	
			3.0	1.3	1.9	2.2	1.3	2.2	1.3	2.2	
			4.5	1.9	2.7	3.1	1.9	3.1	1.9	3.1	
			5.5	2.2	3.3	3.6	2.2	3.6	2.2	3.6	
V _T -	Negative		1.65	0.2	0.5	0.8	0.2	0.8	0.2	0.8	V
	Input Threshold		2.3	0.4	0.75	1.15	0.4	1.15	0.4	1.15	
	Voltage		2.7	0.5	0.87	1.4	0.5	1.4	0.5	1.4	
			3.0	0.6	1.0	1.5	0.6	1.5	0.6	1.5	
			4.5	1.0	1.5	2.0	1.0	2.0	1.0	2.0	
			5.5	1.2	1.9	2.3	1.2	2.3	1.2	2.3	
V _H	Input		1.65	0.1	0.48	0.9	0.1	0.9	0.1	0.9	V
	Hysteresis Voltage		2.3	0.25	0.75	1.1	0.25	1.1	0.25	1.1	
			2.7	0.3	0.83	1.15	0.3	1.15	0.3	1.15	
			3.0	0.4	0.93	1.2	0.4	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	1.7	
V _{OH}	High-Level	$I_{OH} = -100 \mu A$	1.65 to 5.5	V _{CC} – 0.1	V _{CC}	0Y	V _{CC} - 0.1	VÞ.	V _{CC} - 0.1	-	V
	Output Voltage	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52	(to	1.29	-	1.29	-	
	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1	9,	1.9	-	1.9	-	
	VIL	$I_{OH} = -12 \text{ mA}$	2.7	2.2	2.4	2	2.2	-	2.2	-	
		$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7)/-	2.4	-	2.4	-	
		$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5	-	2.3	-	2.3	-	
		$I_{OH} = -32 \text{ mA}$	4,5	3.8	4	-	3.8	-	3.8	-	
V_{OL}	Low-Level	$I_{OL} = 100 \mu\text{A}$	1.65 to 5.5	<\\-\-\.	-	0.1	-	0.1	-	0.1	V
	Output Voltage	I _{OL} = 4 mA	1.65	_	0.08	0.24	-	0.24	-	0.24	
	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.3	
		I _{OL} = 12 mA	2.7	-	0.22	0.4	-	0.4	-	0.4	
	415	I _{OL} = 16 mA	3.0	-	0.28	0.4	-	0.4	-	0.4	
		I _{OL} = 24 mA	3.0	-	0.38	0.55	-	0.55	-	0.55	
		I _{OL} = 32 mA	4.5	-	0.42	0.55	-	0.55	-	0.55	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	_	I	±0.1	-	±1.0	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1	-	10	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	-	-	1	-	10	-	10	μА

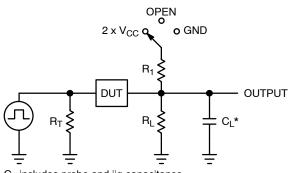
AC ELECTRICAL CHARACTERISTICS

				٦	Γ _A = 25°()	-40°C ≤ 1	Γ _A ≤ 85°C	–55°C ≤ T	_A ≤ 125°C		
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit	
tPLH, tPHL	tPHL Delay, A to Y	$RL = 1 M\Omega$, CL = 15 pF	1.65 to 1.95	-	7.1	13	-	14.5	-	15.5	ns	
	(Figures 3 and 4)	RL = 1 M Ω , CL = 15 pF	2.3 to 2.7	_	4.3	7.4	-	8.1	=	9.1		
	RL = 500 Ω,		CL = 15 pF	CL = 15 pF	3.0 to 3.6	-	3.3	5	_	5.5	-	6.5
			4.5 to 5.5	-	2.7	4.1	_	4.5	-	5.5		
			3.0 to 3.6	-	4	6	-	6.6	-	7.6		
		CL = 50 pF	4.5 to 5.5	-	3.2	4.9	_	5.4	-	6.4		

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V _{CC} = 5.5 V, V _I = 0 V or V _{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_{IN} = 0 V or V_{CC}	11 12.5	pF
Average power o	defined as the value of the internal equivalent capa is operating current can be obtained by the equation consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in}$) $I_{CC} \cdot V_{CC}$.	citance which is calculated from the operating current in I _{CC(OPR)} = C _{PD} · V _{CC} · f _{in}) I _{CC} . C _{PD} is used to de	ent consumption with etermine the no-load	out load.

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in}$) I_{CC} . C_{PD} is used to determine the no–load dynamic



X = Don't Care

Test

t_{PLH} / t_{PHL}

t_{PLZ} / t_{PZL}

 t_{PHZ} / t_{PZH}

Switch

Position

Open 2 x V_{CC}

GND

 C_L, pF

See AC Characteristics Table

See AC Characteristics Table

See AC Characteristics Table

 $\mathsf{R}_\mathsf{L}, \Omega$

 R_1, Ω

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit

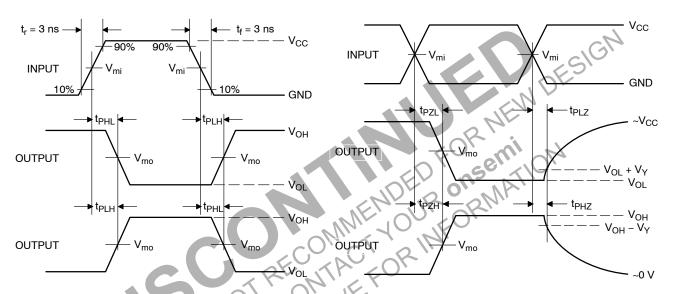


Figure 4. Switching Waveforms

	11000125	V _m		
V _{CC} , V	V_{mi}, V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} / 2	V _{CC} / 2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} / 2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} / 2	V _{CC} / 2	0.3

ORDERING INFORMATION

Device	Package	Specific Device Code	Pin1 Orientation (See below)	Shipping [†]
NL27WZ14DFT2G-L22348	SC-88	MA	Q4	3000 / Tape & Reel
NLV27WZ14DFT2G*	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DTT1G	TSOP-6	MA	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel





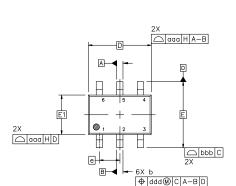
^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





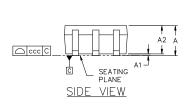
SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

DATE 18 APR 2024



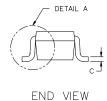
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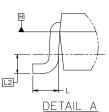
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

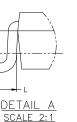


6X 0.30 -

TOP VIEW







GENERIC MARKING DIAGRAM*



DIM	MIN.	MAX.				
Α		1.10				
A1	0.00		0.10			
A2	0.70	0.90	1.00			
b	0.15	0.15 0.20				
С	0.08	0.15	0.22			
D	2.00 BSC					
E	2.10 BSC					
E1	1.25 BSC					
е		0.65 BSC	>			
L	0.26	0.36	0.46			
L2		0.15 BSC				
aaa		0.15				
bbb		0.30				
ccc		0.10				
ddd		0.10				

MILLIMETERS

RECOMMENDED MOUNTING FOOTPRINT*

6X 0.66

2.50

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXX = Specific Device Code

= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65	5P	PAGE 1 OF 4

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SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P		PAGE 2 OF 4	

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NOTE 5

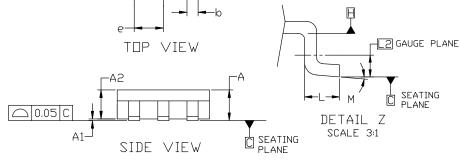
TSOP-6 3.00x1.50x0.90, 0.95P **CASE 318G ISSUE W**

DATE 26 FEB 2024

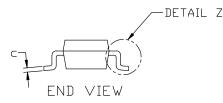


- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
 LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

 5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



MILLIMETERS				
DIM	MIN	NDM	MAX	
Α	0.90	1.00	1.10	
A1	0.01	0.06	0.10	
A2	0.80	0.90	1.00	
b	0.25	0.38	0.50	
C	0.10	0.18	0.26	
D	2.90	3.00	3.10	
Е	2.50	2.75	3.00	
E1	1.30	1.50	1.70	
е	0.85	0.95	1.05	
L	0.20	0.40	0.60	
L2	0.25 BSC			
М	0°		10°	



		-	-	6X -0.60
1				
3.20				6X ⊏0.95
<u> </u>				
	1			
		-	<u>►1</u> 0	.95 ITCH

RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.

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DESCRIPTION:	TSOP-6 3.00x1.50x0.90, 0.95P		PAGE 1 OF 6	

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TSOP-6 3.00x1.50x0.90, 0.95P CASE 318G ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code XXX = Specific Device Code

A =Assembly Location M = Date Code
Y = Year ■ = Pb-Free Package

W = Work Week
■ Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	STYLE 10: PIN 1. D(OUT)+ 2. GND 3. D(OUT)- 4. D(IN)- 5. VBUS 6. D(IN)+	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O
STYLE 13: PIN 1. GATE 1 2. SOURCE 2 3. GATE 2 4. DRAIN 2 5. SOURCE 1 6. DRAIN 1	STYLE 14: PIN 1. ANODE 2. SOURCE 3. GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 6. CATHODE/DRAIN	PIN 1. ANODE PIN 2. SOURCE 3. GATE 4. DRAIN	E 16: 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 17: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR	

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